

CY7C1399BN

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Pin Configurations

Figure 1. 28-pin TSOP pinout (Top View)

TSO Top Vi	-
$22 \\ 23 \\ 24 \\ 25 \\ 26 \\ 27 \\ 28 \\ 1 \\ 2 \\ 3 \\ 4 \\ 5 \\ 6 \\ 7 $	21 A ₀ 20 CE 19 I/O7 18 I/O6 17 I/O5 16 I/O3 14 GND 13 I/O2 12 I/O1 11 I/O2 12 I/O1 10 A14 9 A13 8 A12



 SOJ Top View

 A₆
 1
 28
 VCC

 A₆
 2
 27
 WE

 A₇
 3
 26
 A₄

 A₈
 4
 25
 A₃

 A₉
 5
 24
 A₂

 A10
 6
 23
 A₁

 A11
 7
 22
 OE

 A12
 8
 21
 A₀

 A13
 9
 20
 CE

 A14
 10
 19
 I/O₇

 I/O₀
 11
 18
 I/O₆

 I/O₁
 12
 17
 I/O₅

 I/O₂
 13
 16
 I/O₄

 GND
 14
 15
 I/O₃

Selection Guide

Description	Condition	-12	-15
Maximum access time (ns)		12	15
Maximum operating current (mA)		55	50
Maximum CMOS standby current (µA)	Commercial	500	-
	Commercial (L)	50	-
	Industrial	500	500
	Automotive-A	-	500



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature	–65 °C to +150 °C
Ambient temperature with power applied	–55 °C to +125 °C
Supply voltage on V_{CC} to relative GND ^[1]	–0.5 V to +4.6 V
DC voltage applied to outputs in high Z State ^[1]	–0.5 V to V _{CC} + 0.5 V
DC input voltage [1]	–0.5 V to V _{CC} + 0.5 V

Output current into outputs (LOW)	
Static discharge voltage	
(per MIL-STD-883, Method 3015) >2001 V	
Latch-up current>200 mA	

Operating Range

Range	Ambient Temperature	V _{cc}
Commercial	0 °C to +70 °C	$3.3~V\pm300~mV$
Industrial	–40 °C to +85 °C	
Automotive-A	–40 °C to +85 °C	

Electrical Characteristics

Over the Operating Range

Parameter ^[1]	Description	Test Conditions			-12		-15	11
Parameter	Description			Min	Max	Min Max		Unit
V _{OH}	Output HIGH voltage	Min V _{CC} , $I_{OH} = -2$.	0 mA	2.4	-	2.4	-	V
V _{OL}	Output LOW voltage	Min V _{CC} , I _{OL} = 4.0 n	۱A	-	0.4	-	0.4	V
V _{IH}	Input HIGH voltage			2.2	V _{CC} + 0.3	2.2	V _{CC} + 0.3	V
V _{IL} ^[1]	Input LOW voltage			-0.3	0.8	-0.3	0.8	V
I _{IX}	Input leakage current			-1	+1	-1	+1	μA
I _{OZ}	Output leakage current	$GND \le V_{IN} \le V_{CC}, C$	utput disabled	-5	+5	-5	+5	μA
I _{CC}	V _{CC} operating supply current	$\begin{array}{l} \text{Max V}_{\text{CC}}, \text{I}_{\text{OUT}} = 0 \text{ mA}, \\ \text{f} = \text{f}_{\text{MAX}} = 1/\text{t}_{\text{RC}} \end{array}$		-	55	-	50	mA
I _{SB1}	Automatic CE power-down	$Max V_{CC}, \overline{CE} \ge V_{IH},$	Commercial	_	5	-	-	mA
	current – TTL inputs	$V_{IN} \ge V_{IH}$, or $V_{IN} \le V_{IL}$,	Commercial (L)	_	4	-	-	mA
		$f = f_{MAX}$	Industrial	_	5	-	5	mA
			Automotive-A	_	_	-	5	mA
I _{SB2}	Automatic CE Power-down	<u>Ma</u> x V _{CC} ,	Commercial	-	500	-	_	μA
	current – CMOS inputs ^[2]	$\frac{\overline{CE}}{V_{IN}} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V}, \text{ or}$	Commercial (L)	-	50	-	_	μA
		V _{IN} ≤ 0.3 V,	Industrial	-	500	-	500	μA
		$\label{eq:WE} \begin{split} & \widetilde{WE} \geq V_{CC} - 0.3 \ V \ or \\ & WE \leq 0.3 \ V, \\ & f = f_{MAX} \end{split}$	Automotive-A	-	_	-	500	μA

- Notes
 Minimum voltage is equal to -2.0 V for pulse durations of less than 20 ns.
 Device draws low standby current regardless of switching on the addresses.

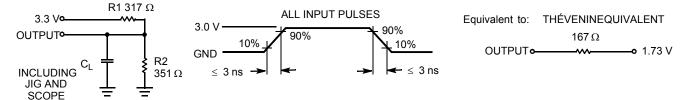


Capacitance

Parameter ^[3]	Description	Test Conditions	Max	Unit
C _{IN} : Addresses	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 3.3 V	5	pF
C _{IN} : Controls			6	pF
C _{OUT}	Output capacitance		6	pF

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms ^[4]



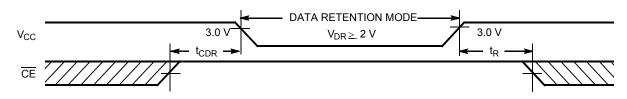
Data Retention Characteristics

(Over the Operating Range - L version only)

Parameter	Description	Conditions	Min	Max	Unit
V _{DR}	V _{CC} for data retention		2.0	_	V
I _{CCDR}	Data retention current	$V_{CC} = V_{DR} = 2.0 V,$	0	20	μΑ
t _{CDR}	Chip deselect to data retention time	$\overrightarrow{CE} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	0	_	ns
t _R	Operation recovery time		t _{RC}	Ι	ns

Data Retention Waveform

Figure 4. Data Retention Waveform



Notes

- Tested initially and after any design or process changes that may affect these parameters.
 Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and capacitance C_L = 30 pF.



Switching Characteristics

Over the Operating Range

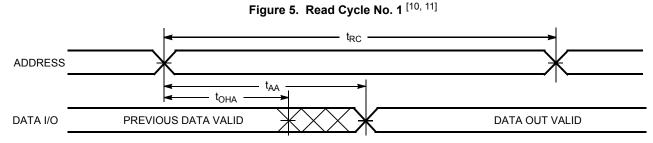
Parameter ^[5]	Description	-	12	-	15	Unit		
Parameter ¹⁰¹	Description	Min	Max	Min	Мах			
Read Cycle								
t _{RC}	Read cycle time	12	-	15	-	ns		
t _{AA}	Address to data valid	-	12	-	15	ns		
t _{OHA}	Data hold from address change	3	-	3	-	ns		
t _{ACE}	CE LOW to data valid	-	12	-	15	ns		
t _{DOE}	OE LOW to data valid	-	5	-	6	ns		
t _{LZOE}	OE LOW to low Z ^[6]	0	-	0	-	ns		
t _{HZOE}	OE HIGH to high Z ^[6, 7]	-	5	-	6	ns		
t _{LZCE}	CE LOW to low Z ^[6]	3	-	3	-	ns		
t _{HZCE}	CE HIGH to high Z ^[6, 7]	-	6	-	7	ns		
t _{PU}	CE LOW to power-up	0	-	0	-	ns		
t _{PD}	CE HIGH to power-down	-	12	-	15	ns		
Write Cycle ^{[8, 9}	9]					·		
t _{WC}	Write cycle time	12	-	15	-	ns		
t _{SCE}	CE LOW to write end	8	-	10	-	ns		
t _{AW}	Address setup to write end	8	-	10	-	ns		
t _{HA}	Address hold from write end	0	-	0	-	ns		
t _{SA}	Address setup to write start	0	-	0	-	ns		
t _{PWE}	WE pulse width	8	_	10	-	ns		
t _{SD}	Data setup to write end	7	_	8	-	ns		
t _{HD}	Data hold from write end	0	-	0	-	ns		
t _{HZWE}	WE low to high Z ^[8]	_	7	_	7	ns		
t _{LZWE}	WE high to low Z ^[6]	3	-	3	_	ns		

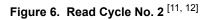
Notes

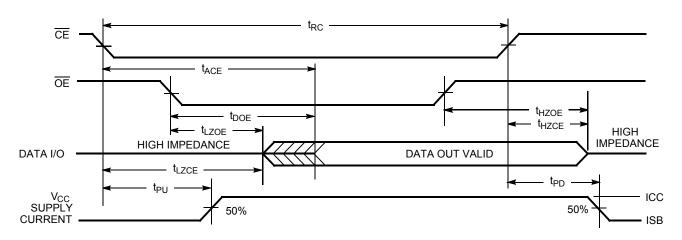
5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} best conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and capacitance C_L = 30 pF.
 At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE} are specified with C_L = 5 pF as in AC Test Loads. Transition is measured ±500 mV from steady state voltage.
 The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
 The minimum write cycle time for write cycle #3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms







Notes

- 10. <u>Device</u> is continuously selected. \overline{OE} , $\overline{CE} = V_{||L}$. 11. WE is HIGH for read cycle.

12. Address valid prior to or coincident with \overline{CE} transition LOW.



Switching Waveforms (continued)

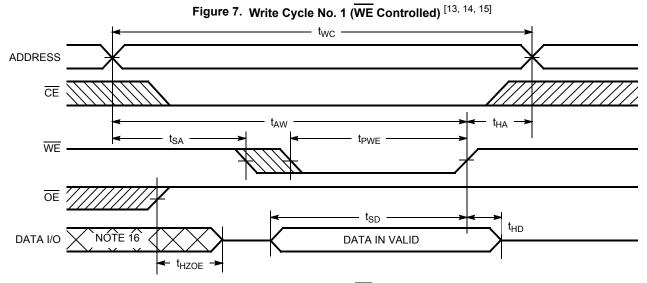
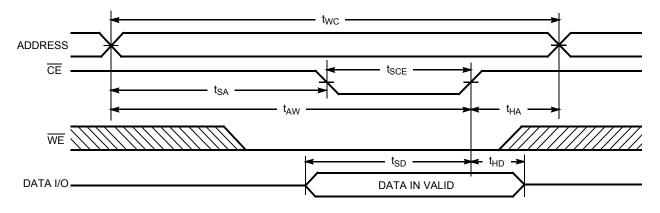


Figure 8. Write Cycle No. 2 (CE Controlled) ^[13, 14, 15]

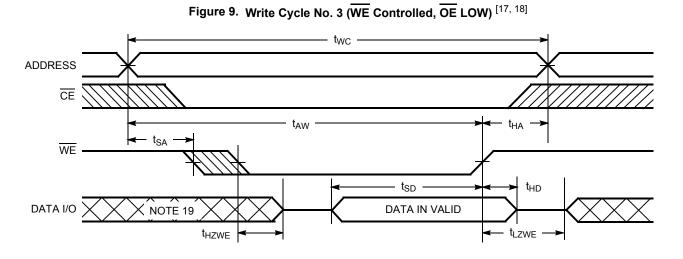


Notes

13. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
14. Data I/O is high impedance if OE = V_{IH}.
15. If CE goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.
16. During this period, the I/Os are in the output state and input signals should not be applied.



Switching Waveforms (continued)



Notes

17. The minimum write cycle time for write cycle #3 ($\overline{\text{WE}}$ controlled, $\overline{\text{OE}}$ LOW) is the sum of t_{HZWE} and t_{SD} . 18. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ HIGH, the output remains in a high-impedance state. 19. During this period, the I/Os are in the output state and input signals should not be applied.



Truth Table

CE	WE	OE	Input/Output	Mode	Power
Н	Х	Х	High Z	Deselect/Power-down	Standby (I _{SB})
L	Н	L	Data Out	Read	Active (I _{CC})
L	L	Х	Data In	Write	Active (I _{CC})
L	Н	Н	High Z	Deselect, Output disabled	Active (I _{CC})



Ordering Information

Cypress offers other versions of this type of product in many different configurations and features. The following table contains only the list of parts that are currently available.

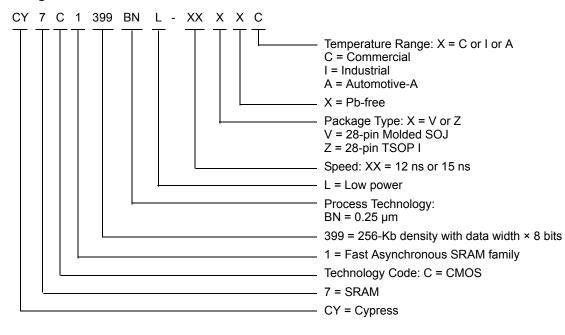
For a complete listing of all options, visit the Cypress website at www.cypress.com and refer to the product summary page at http://www.cypress.com/products or contact your local sales representative.

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Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
12	CY7C1399BN-12VXC	51-85031	28-pin molded SOJ (Pb-free)	Commercial
	CY7C1399BN-12ZXC	51-85071	28-pin TSOP I (Pb-free)	
	CY7C1399BNL-12ZXC		28-pin TSOP I (Pb-free)	
	CY7C1399BN-12VXI	51-85031	28-pin molded SOJ (Pb-free)	Industrial
15	CY7C1399BN-15ZXI	51-85071	28-pin TSOP I (Pb-free)	Industrial
	CY7C1399BN-15VXA	51-85031	28-pin molded SOJ (Pb-free)	Automotive-A

Contact your local sales representative regarding availability of these parts.

Ordering Code Definitions



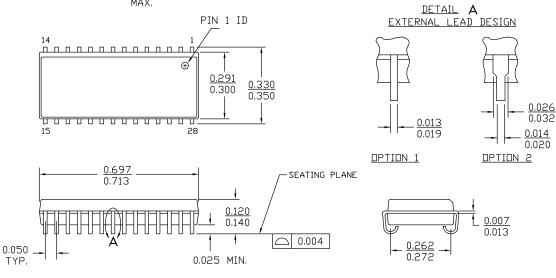


Package Diagrams

Figure 10. 28-pin SOJ (300 Mils) V28.3 (Molded SOJ V21) Package Outline, 51-85031

NDTE :

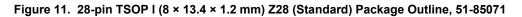
- 1. JEDEC STD REF MOO88
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE
- 3. DIMENSIONS IN INCHES $\underline{\text{MIN.}}_{\text{MAX.}}$

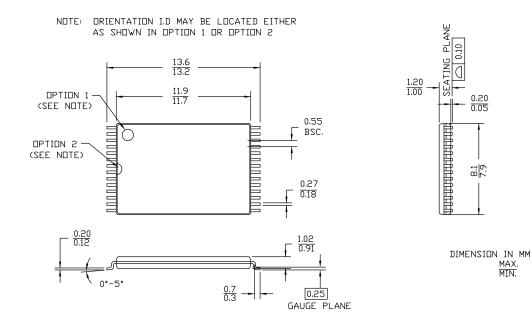


51-85031 *E



Package Diagrams (continued)





51-85071 *I



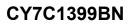
Acronyms

Acronym	Description
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
WE	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure	
°C	degree Celsius	
MHz	megahertz	
μA	microampere	
mA	milliampere	
mV	millivolt	
mW	milliwatt	
ns	nanosecond	
pF	picofarad	
V	volt	
W	watt	





Document History Page

Document Title: CY7C1399BN, 256-Kbit (32 K × 8) Static RAM Document Number: 001-06490					
Revision	ECN	Orig. of Change	Submission Date	Description of Change	
**	423877	NXR	See ECN	New data sheet.	
*A	498575	NXR	See ECN	Added Automotive-A range Removed I _{OS} parameter from DC Electrical Characteristics table Updated Ordering Information table.	
*В	2896382	AJU	03/19/2010	Removed obsolete part numbers from Ordering Information table and updated package diagrams.	
*C	3053362	PRAS	10/08/2010	Removed pruned part numbers CY7C1399BNL-15VXC and CY7C1399BNL-15VXCT. Added Ordering Code Definitions.	
*D	3383869	TAVA	09/26/2011	Added Commercial temperature range under Features section on page 1. Removed reference to AN1064-SRAM System Design Guidelines on page 1. Modified the notes in figures under Read cycle and Write cycle sections. Updated template according to current Cypress standards. Rearranged sections for better clarity. Revised package diagrams. Added Acronyms and Units of measure.	
*E	4121360	VINI	09/12/2013	Updated in new template.	
				Completing Sunset Review.	



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